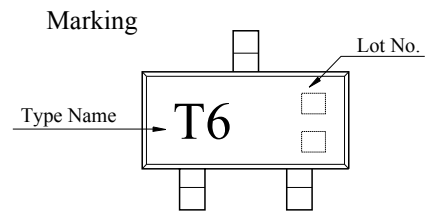
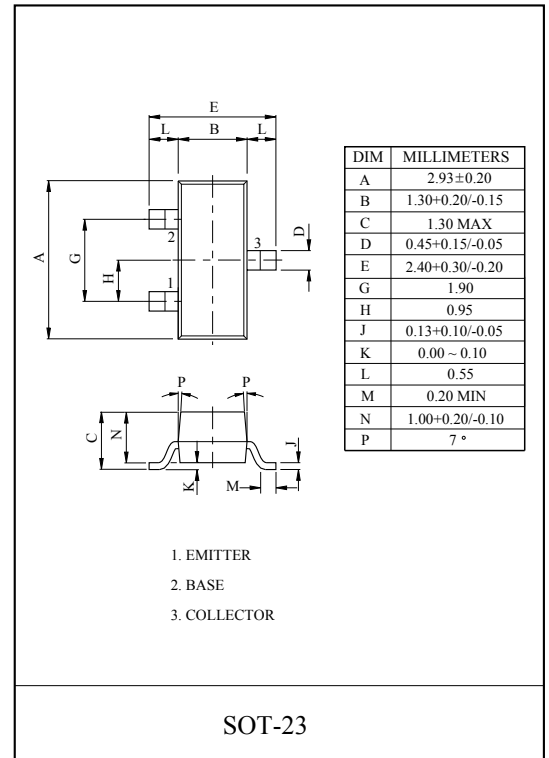


GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-110	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-100	mA
Emitter Current	I_E	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-100	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-110	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -90V, I_E = 0$	-	-	-100	nA
		$V_{CB} = -90V, I_E = 0, T_a = 150^\circ C$	-	-	-50	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-200	nA
DC Current Gain	h_{FE}	$V_{CE} = -1V, I_C = -10mA$	30	-	-	
		$V_{CE} = -1V, I_C = -25mA$	30	-	-	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -25mA, I_B = -2.5mA$	-	-	-0.9	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -25mA, I_B = -2.5mA$	-	-	-0.25	V
		$I_C = -75mA, I_B = -7.5mA$	-	-	-0.9	
Transition Frequency	f_T	$I_C = -25mA, V_{CE} = -5V, f = 100MHz$	50	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	3	-	pF